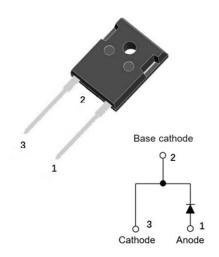




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F(135°C)}	40A
Q _C	225nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-247AC

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112040NYG5
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _c =25°C	l _F	А	87
Continuous forward current @ T _C =135°C	IF.	A	40
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	400
Power Dissipation@ T _C =25°C	D		300
Power Dissipation@ T _C =110°C	Ртот	W	130
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	800
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



YJD112040NYG5

■Electrical Characteristics (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min.	Тур.	Max.					
Reverse voltage (DC)	V_{DC}	V	I _R =0.25mA, T _j =25°C	> 1200	-	-					
	V _F	V	I _F =40A, T _j =25°C	-	1.37	1.60					
Forward voltage			V _F V	r _F V	V _F V	I _F =40A, T _j =175°C	-	1.95	-		
Reverse current I _R		μΑ	V _R =1200V, T _j =25°C	-	0.5	25					
	I _R		V _R =1200V, T _j =175°C	-	60	-					
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C, Q_C = $\int_0^{VR} C(V) dV$	-	225	-					
								V _R =0V, f=1MHZ	-	3170	-
Total capacitance C	С	pF	V _R =400V, f=1MHZ	-	211	-					
			V _R =800V, f=1MHZ	-	160	-					
Capacitance stored energy	Ec	μJ	V _R =800V	-	64	-					

■Thermal Characteristics

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{ heta J-C}$	°C W	0.50

■Typical Characteristics (Typical)

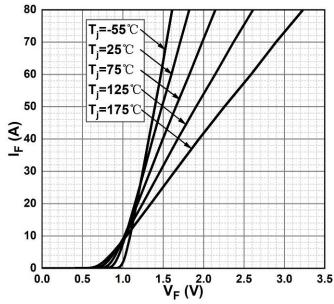


Figure 1. Forward Characteristics

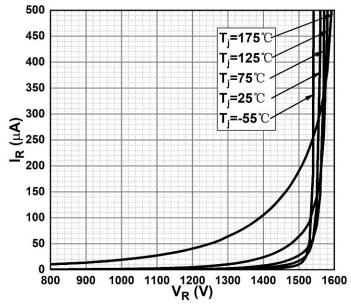
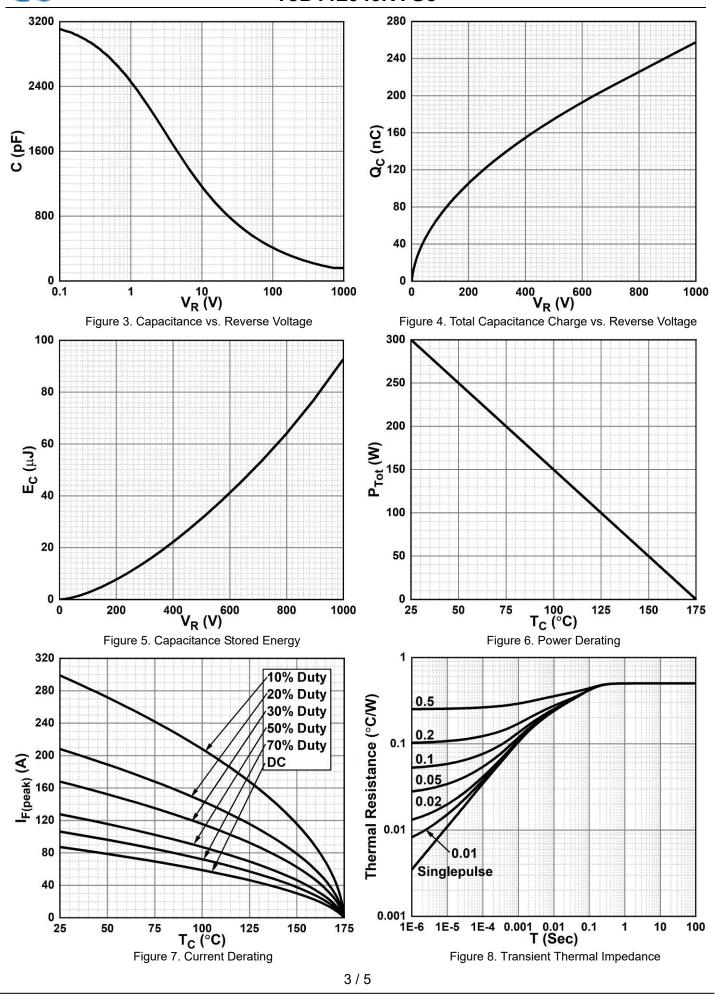


Figure 2. Reverse Characteristics

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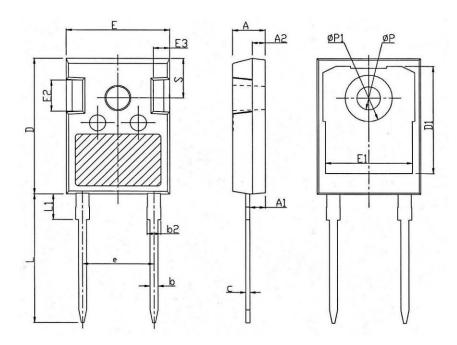






■Outline Dimensions

TO-247AC



TO-247AC				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15BSC			



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